

ABSTRACT OF THE DISCLOSURE

A method for inspecting crystal quality of a polysilicon film. First, a substrate covered by a polysilicon layer is provided. Next, a probe light beam having a predetermined wavelength is irradiated through a beam splitter to separate into a first light beam and a second light beam, which is used for irradiating the polysilicon layer. Thereafter, the light intensity of the first light beam and the light intensity of the second light beam reflected from the polysilicon layer are detected to achieve a light intensity ratio. Finally, crystal quality of the polysilicon layer is monitored by the light intensity ratio. An apparatus for inspecting crystal quality of a polysilicon film and the method for controlling the same are also disclosed.